

THE INFLUENCE OF ANNEALING  
IN THE ATMOSPHERE OF ATOMIC  
OXYGEN ON THE PHOTOLUMINESCENCE  
OF ZnO LAYERS IMPLANTED BY As AND N

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S u m m a r y

It is shown that the implantation of films of Zn oxide by acceptor admixtures of arsenic and nitrogen with the subsequent annealing in the atmosphere of atomic oxygen leads to a change in the spectra of photoluminescence (PL). The PL spectra reveal the bands with maxima at 3.33 and 3.29 eV which are caused by the implantation of As and N, respectively.